

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0103M uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

• $V_{DS} = 100V, I_{D} = 3A$

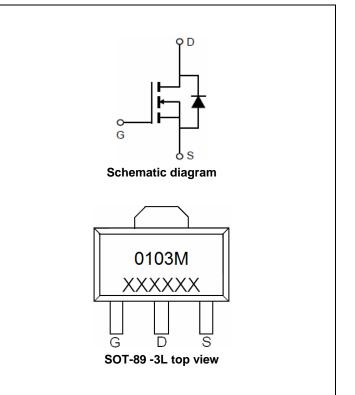
 $R_{DS(ON)}\,{<}160m\Omega\;\textcircled{0}\;V_{GS}{=}10V\quad (Typ:136m\Omega)$

 $R_{DS(ON)}$ <170m Ω @ V_{GS} =4.5V (Typ:140m Ω)

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0103M	NCE0103M	SOT-89-3L	Ø180mm	12mm	1000units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	3	Α
Drain Current-Pulsed (Note 1)	I _{DM}	20	Α
Maximum Power Dissipation	P _D	1.5	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}\!$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	83	°C/W
	00/1		l i

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	٧
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA



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NCE0103M

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.6	1.1	1.8	V	
Drain Source On State Decistance	Б	V _{GS} =10V, I _D =3A	- 136 160		0		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =3A	-	140	170	mΩ	
Forward Transconductance	g _{FS}	$V_{DS}=5V,I_{D}=3A$	-	5	-	S	
Dynamic Characteristics (Note4)			•			•	
Input Capacitance	C _{lss}	\/ 50\/\/ 0\/	-	650	-	PF	
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V,	-	24	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	20	-	PF	
Switching Characteristics (Note 4)			•			•	
Turn-on Delay Time	t _{d(on)}		-	6	-	nS	
Turn-on Rise Time	t _r	V_{DD} =50V, R_L =19 Ω	-	4	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	20	-	nS	
Turn-Off Fall Time	t _f		-	4	-	nS	
Total Gate Charge	Qg	\/ F0\/ 0A	-	20		nC	
Gate-Source Charge	Q_{gs}	V_{DS} =50V, I_{D} =3A, V_{GS} =10V	-	2.1	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	3.3	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	3	Α	

Notes:

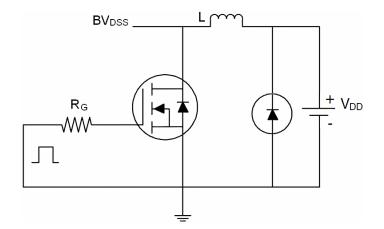
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to productio



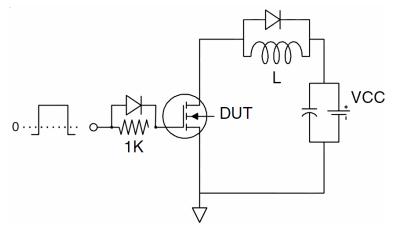
Pb-Free Product

Test Circuit

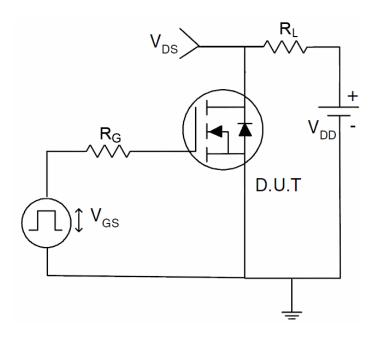
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

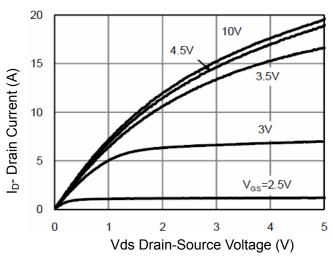


Figure 1 Output Characteristics

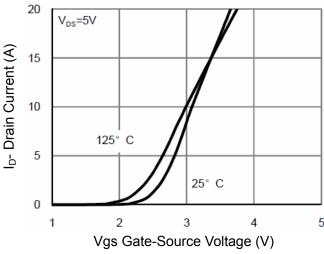


Figure 2 Transfer Characteristics

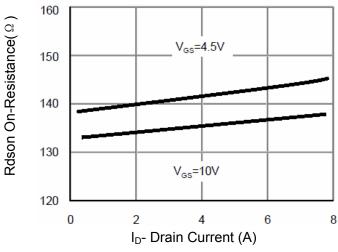


Figure 3 Rdson- Drain Current

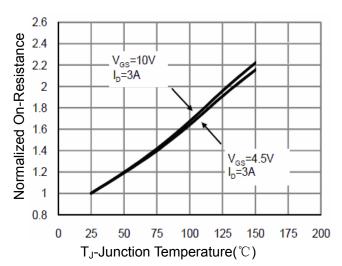


Figure 4 Rdson-JunctionTemperature

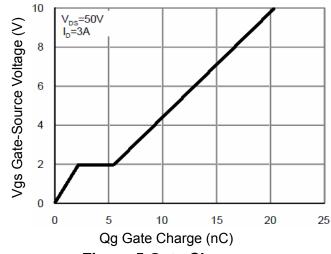


Figure 5 Gate Charge

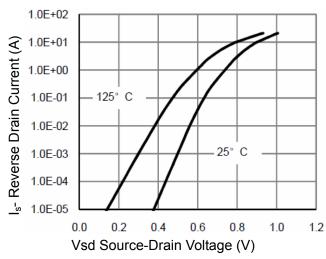


Figure 6 Source- Drain Diode Forward

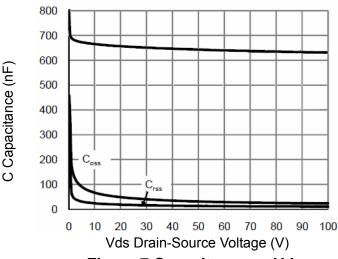


Figure 7 Capacitance vs Vds

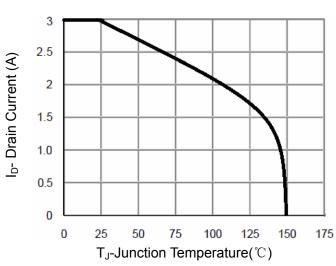


Figure 9 BV_{DSS} vs Junction Temperature

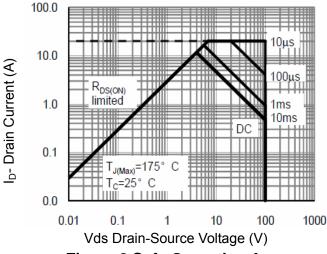


Figure 8 Safe Operation Area

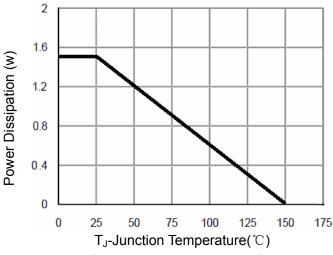


Figure 10 Power De-rating

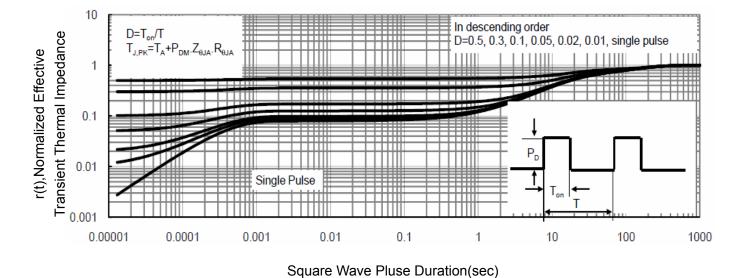
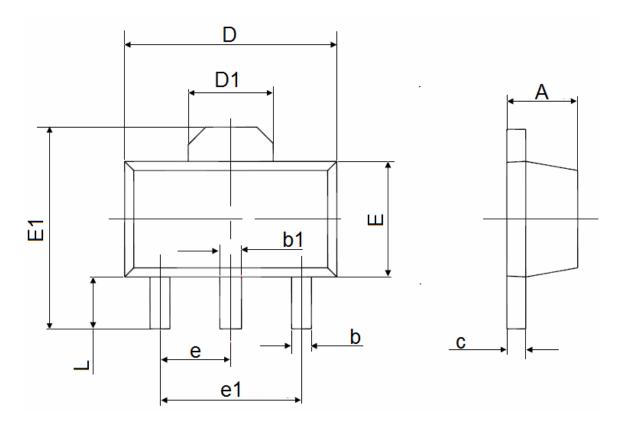


Figure 11 Normalized Maximum Transient Thermal Impedance



SOT-89-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550	REF.	0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500	TYP.	0.060 TYP.		
e1	3.000 TYP.		0.118	TYP.	
L	0.900	1.200	0.035	0.047	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

Pb-Free Product

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